Computational Microelectronics Report (Homework #4)

Professor: Hong, Sung-Min

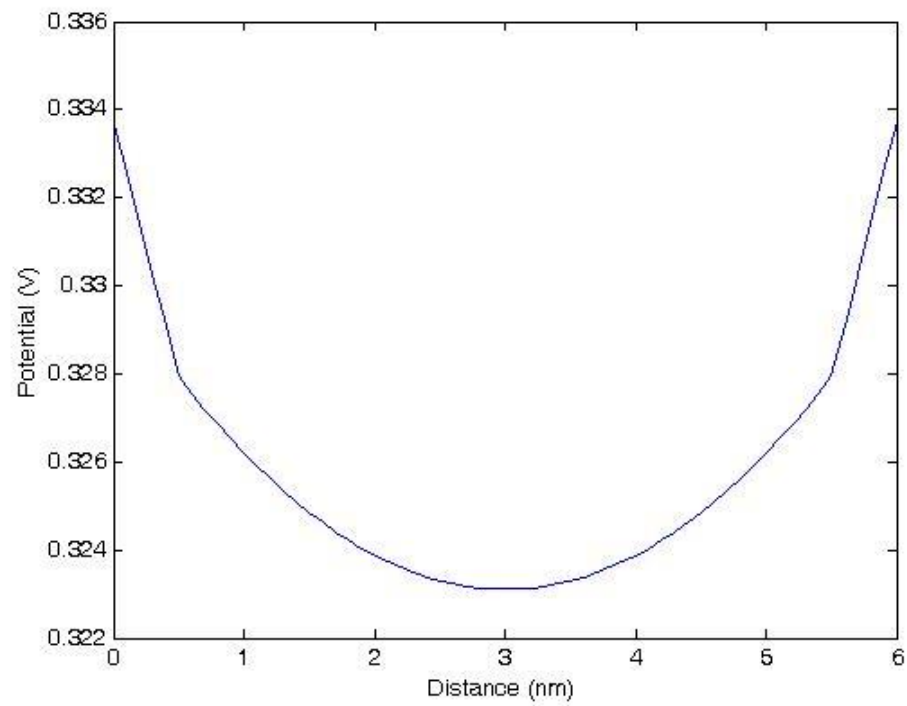Major: Electrical Engineering and Computer Science

Student Number: 20181018
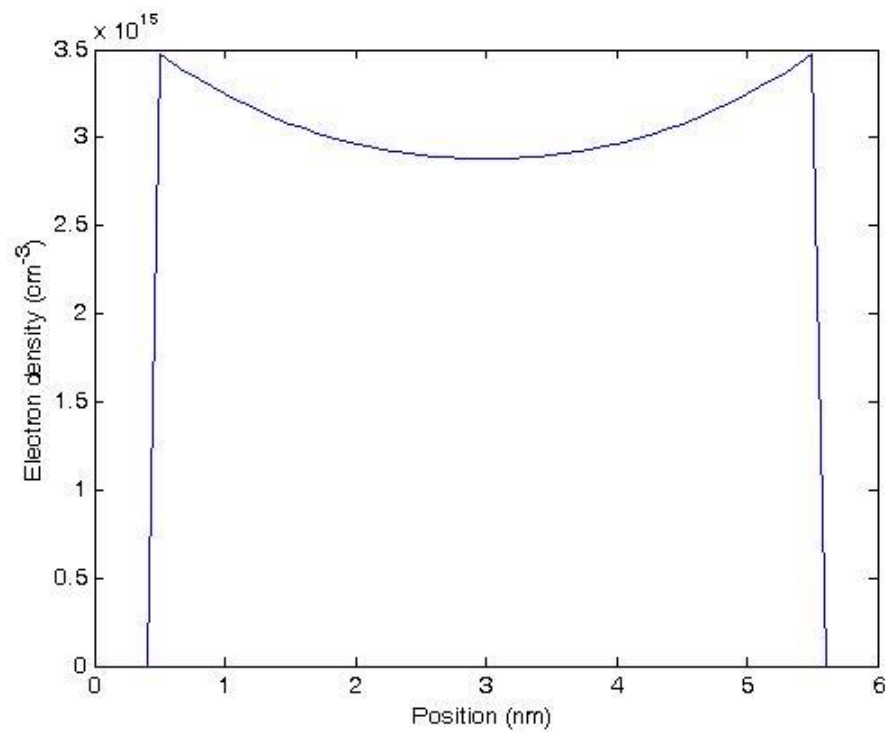
Student Name: Jang, Mi

Submission Date: 2018.10. 01

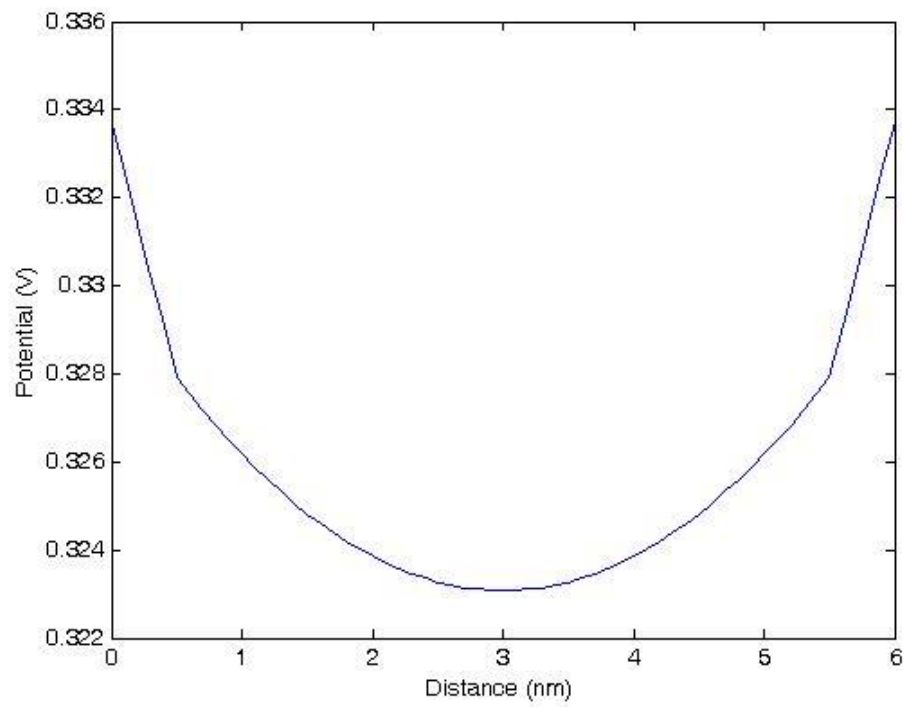1. Electrostatic potential under initial condition (The applied voltage is 0V.)

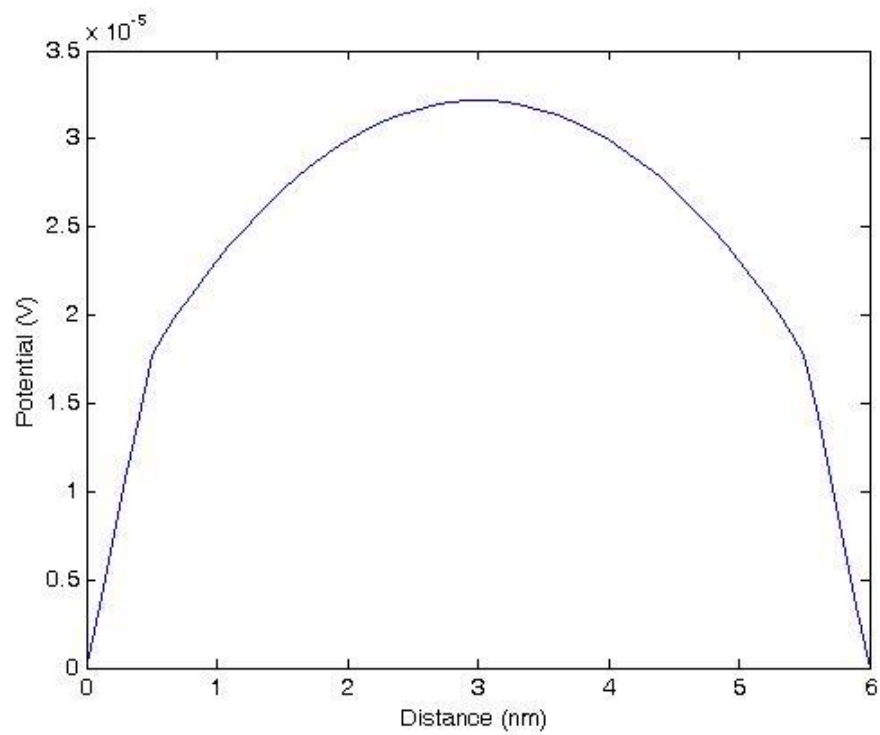2. Electron density under initial condition (The applied voltage is 0V.)

3. Re-calculated potential

3-1. Re-calculated potential

3-2. Difference between 1 and 3-1

The potential in silicon makes the difference because n(x) is so small that it is ignored.

4. Difference for several gate voltages from 0V to 1V